Unitized Semiconductor Devices - Page 1 of 1



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| Inclosure Material: |
|--|
| Plastic |
| Component Name And Quantity: |
| 4 transistor |
| Mounting Method: |
| Press fit |
| Semiconductor Material: |
| Silicon all transistor |
| Voltage Rating In Volts Per Characteristic: |
| 60.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source all transistor |
| Current Rating Per Characteristic: |
| 225.00 milliamperes drain current all transistor |
| Power Rating Per Characteristic: |
| 800.0 milliwatts total power dissipation all transistor |
| Maximum Operating Tempurature Per Measurement Point: |
| 150.0 degrees celsius junction |
| Terminal Type And Quantity: |
| 14 ribbon |
| Shelf Life: |
| N/a |
| Unit Of Measure: |
| |
| Demilitarization: |
| Yes - demil/mli |
| Fiig: |
| A110a0 |
| |